

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 2N3375** is Designed for Class A,B,C Amplifier,Oscillator and Driver Applications Covering the VHF-UHF Region.

FEATURES INCLUDE:

- Isolated Package

MAXIMUM RATINGS

I_C	1.5 A
V_{CE}	40 V
P_{DISS}	11.6 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	15 $^\circ\text{C/W}$

PACKAGE STYLE TO-60(ISOLATED)

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.090/2,29	.110/2,79
B	.185/4,70	.215/5,46
C	.420/10,67	.440/11,18
D	.030/0,76	.046/1,17
E	.320/8,13	.360/9,14
F	.090/2,29	.135/3,43
G	.215/5,46	.320/8,13
H		.480/12,19
I	.420/10,67	.455/11,56

1 = EMITTER 2 = BASE
3 = COLLECTOR

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200\text{ mA}$	40			V
BV_{CEX}	$V_{BE} = -1.5\text{ V}$ $I_C = 100\text{ mA}$	65			V
BV_{CBO}	$I_C = 500\ \mu\text{A}$	65			V
I_{CEO}	$V_{CE} = 30\text{ V}$			100	μA
I_{EBO}	$V_{EB} = 4.0\text{ V}$			100	μA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 250\text{ mA}$	10			---
$V_{CE(SAT)}$	$I_C = 500\text{ mA}$ $I_B = 100\text{ mA}$			1.0	V
C_{ob}	$V_{CB} = 30\text{ V}$ $f = 1.0\text{ MHz}$			10	pF
f_t	$V_{CE} = 28\text{ V}$ $I_C = 150\text{ mA}$ $f = 100\text{ MHz}$		500		MHz
P_{out} G_P η	$V_{CE} = 28\text{ V}$ $P_{in} = 1.0\text{ W}$ $f = 400\text{ MHz}$	3.0 4.8 40			W dB %